

DMTH6010LPSWQ

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

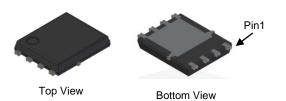
BV _{DSS}	R _{DS(ON)} max	I _{D MAX} T _C = +25°С	
60V	8mΩ @ V _{GS} = 10V	80A	
	$12m\Omega @ V_{GS} = 4.5V$	64.5A	

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

PowerDI5060-8 (SWP) (Type Q)

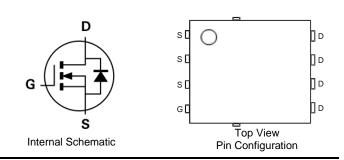


Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- Low R_{DS(ON)}—Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH6010LPSWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Packaging
Type Q) 2500 / Tape & Reel
(

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D11 = Manufacturer's Marking
TH6010LSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
	T _A = +25°C	ID	15.5	٨
Continuous Drain Current, $V_{GS} = 10V$ (Note 5)	T _A = +100°C		11	A
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_{C} = +25^{\circ}C$	ID	80	٨
	$T_{C} = +100^{\circ}C$		56	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	320	A
Maximum Continuous Body Diode Forward Current (Note 6)		Is	80	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	320	A
Avalanche Current, L=0.1mH		I _{AS}	20	А
Avalanche Energy, L=0.1mH		E _{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	52	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	75	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	2.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	·						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Statia Drain Course Or Desistance		_	5.3	8	mΩ	V _{GS} = 10V, I _D = 20A	
Static Drain-Source On-Resistance	R _{DS(ON)}		7.9	12		V _{GS} = 4.5V, I _D = 20A	
Diode Forward Voltage	V _{SD}		0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)						÷	
Input Capacitance	Ciss	_	2090	—		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	38.5	—			
Gate Resistance	Rg	_	0.59	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qq		19.3	_		V _{DS} = 30V, I _D = 20A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	41.3	—	nC		
Gate-Source Charge	Q _{gs}		6	_	nC		
Gate-Drain Charge	Q _{gd}	_	8.8	—			
Turn-On Delay Time	t _{D(ON)}	_	5.7	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_g = 3\Omega$	
Turn-On Rise Time	t _R	_	4.3	_			
Turn-Off Delay Time	t _{D(OFF)}		23.4	_	ns		
Turn-Off Fall Time	t _F	_	9.7	—			
Body Diode Reverse Recovery Time	t _{RR}	_	35.4	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}		38.2	—	nC	−I _F = 20A, di/dt = 100A/μs	

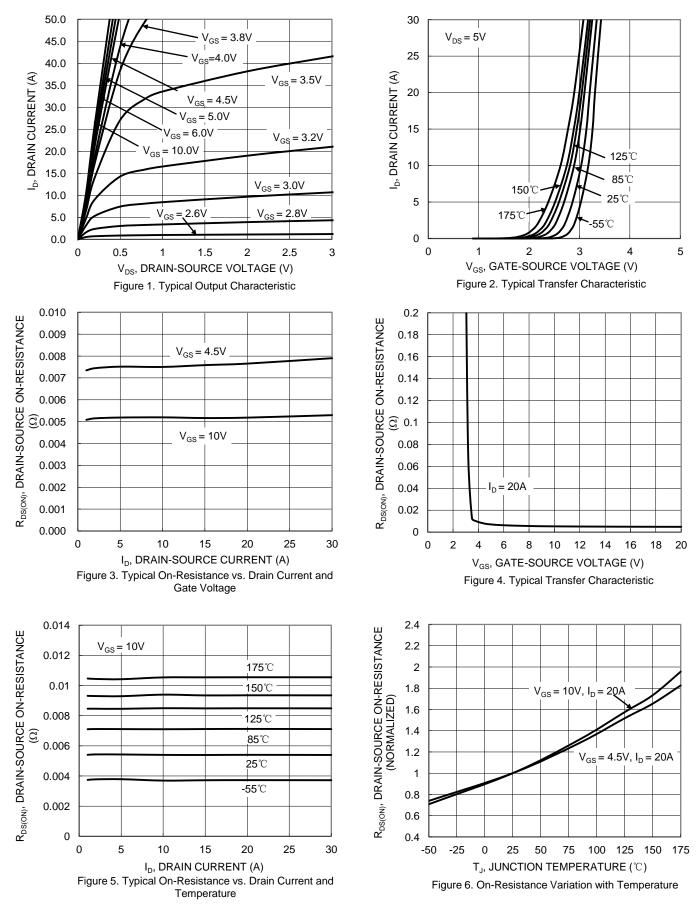
Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

Notes:



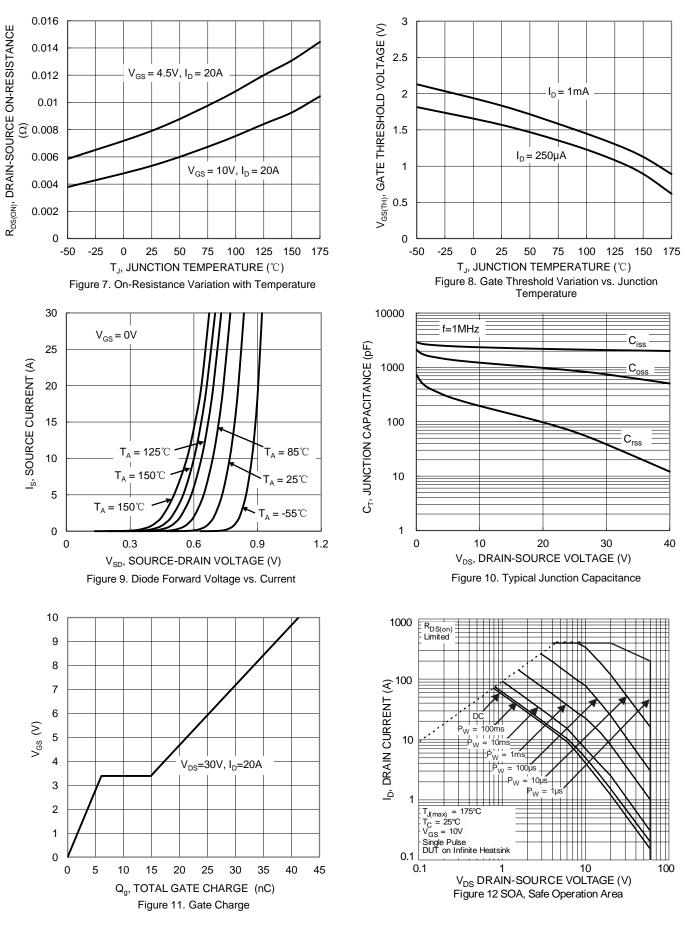
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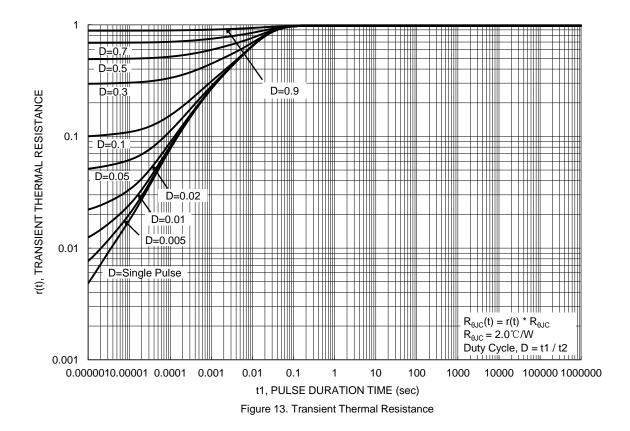
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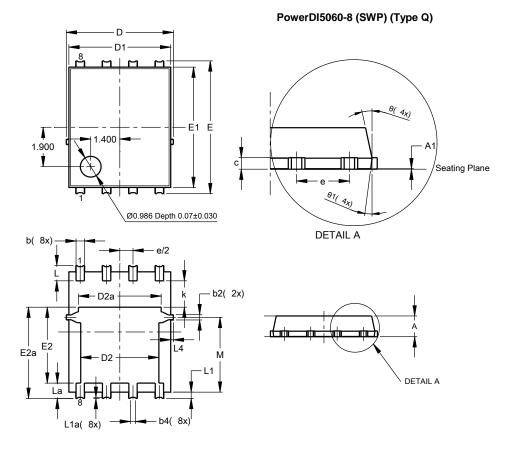






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

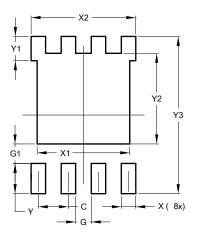


Pov	PowerDI5060-8 (SWP) (Type Q)				
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	0.25REF				
С	0.230 0.330 0.277				
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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